



DSS3515M

15V LOW V_{CE(sat)} PNP SURFACE MOUNT TRANSISTOR

Features

- Low Collector-Emitter Saturation Voltage, VCE(sat)
- Ultra-Small Leadless Surface Mount Package
- ESD: HBM 8kV, MM 400V
- Complementary NPN Type Available (DSS2515M)
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)

Mechanical Data

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0009 grams (Approximate)

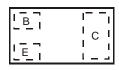
DFN1006-3



Bottom View



Device Symbol



Top View Device Schematic

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS3515M-7	ТВ	7	8	3,000
DSS3515M-7B	TB	7	8	10,000

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com
- 3. For packaging details, go to our website at http://www.diodes.com.

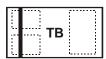
Marking Information

DSS3515M-7



Top View Dot Denotes Collector Side

DSS3515M-7B



Top View Bar Denotes Base and Emitter Side

TB = Product Type Marking Code



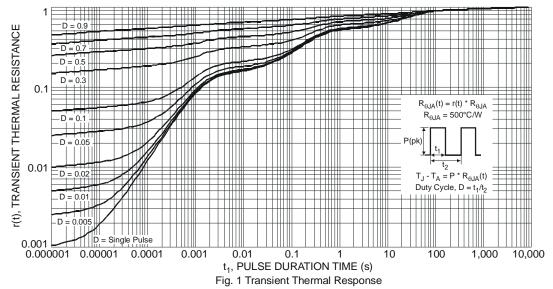
Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-15	V
Collector-Emitter Voltage	V _{CEO}	-15	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current - Continuous	I _C	-500	mA
Peak Pulse Collector Current	I _{CM}	-1	Α
Peak Base Current	I _{BM}	-100	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P _D	250	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ heta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 4. Device mounted on FR-4 PCB with minimum recommended pad layout.



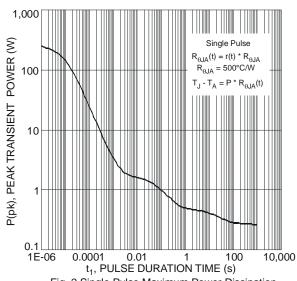


Fig. 2 Single Pulse Maximum Power Dissipation

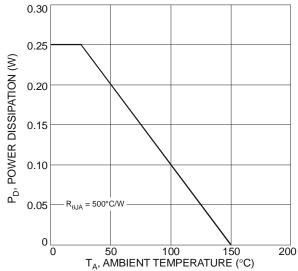


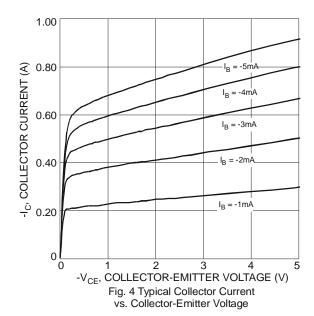
Fig. 3 Power Dissipation vs. Ambient Temperature (Note 4)

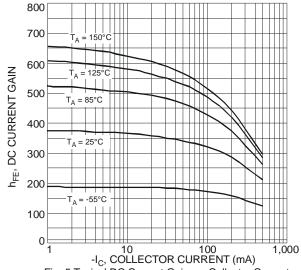


Electrical Characteristics @T_A = 25°C unless otherwise specified

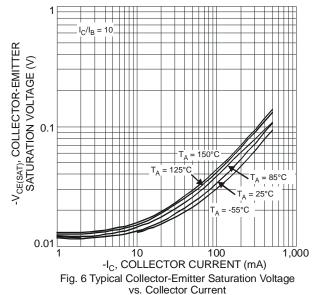
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-15	_		٧	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	-15	_		V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{)EBO}	-6	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	l	_	_	-100	nA	$V_{CB} = -15V, I_{E} = 0$
Collector Cutoff Current	I _{CBO}			-50	μΑ	$V_{CB} = -15V$, $I_E = 0$, $T_A = 150$ °C
Emitter Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -5V, I_C = 0$
ON CHARACTERISTICS (Note 5)						
		200	_	_		$V_{CE} = -2V, I_{C} = -10mA$
DC Current Gain	h _{FE}	150	_	_	_	$V_{CE} = -2V, I_{C} = -100mA$
		90	_			$V_{CE} = -2V, I_{C} = -500mA$
		_	_	-25		$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	-150	mV	$I_C = -200 \text{mA}, I_B = -10 \text{mA}$
		_	—	-250		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	500	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-1.1	V	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	-0.9	V	V _{CE} = -2V, I _C = -100mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	_	_	10	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	100	340	_	MHz	$V_{CE} = -5V, I_{C} = -100mA, f = 100MHz$

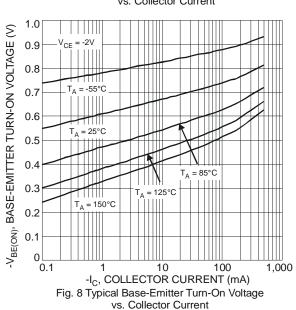
Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.











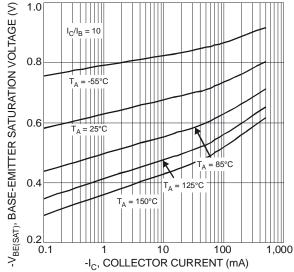


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

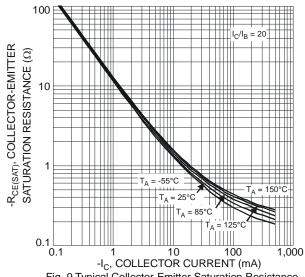
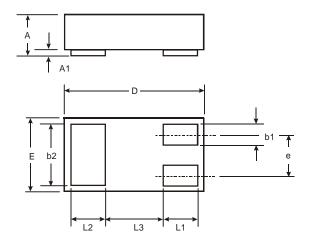


Fig. 9 Typical Collector-Emitter Saturation Resistance vs. Collector Current

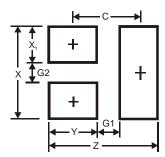
Package Outline Dimensions



DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
E	0.55	0.675	0.60		
е			0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All	All Dimensions in mm				



Suggested Pad Layout



Value (in mm)			
1.1			
0.3			
0.2			
0.7			
0.25			
0.4			
0.7			

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